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Media Advisory

**Innovative Silicon's David Fisch to Present on Z-RAM[®]
Memory Scalability at the 2007 IEEE International SOI
Conference**

to 32nm and Beyond...

2007 IEEE International SOI Conference, INDIAN WELLS, Calif. — October 2, 2007 — Innovative Silicon Inc.(ISi), the developer of Z-RAM[®] high-density memory intellectual property (IP), announced that David Fisch, director of product architecture at ISi, is presenting a paper here entitled "Innovative approach to drive floating body Z-RAM embedded memory to 32 nm and beyond." The invited presentation will open Session 7 – entitled "SOI Memories, FB and Sensors" – at 8:00 a.m. on Thursday, October 4th. The conference runs today through October 4, 2007 at the Miramonte Resort and Spa, Indian Wells, California. For full conference details, see <http://www.soiconference.org> .

During the presentation, Fisch will provide an overview of Z-RAM memory operation basics, discuss the application trends in embedded memory and compare the Z-RAM bit-cell scalability relative to other embedded memory solutions. Bit-cell performance, manufacturability, body capacitance and mitigation techniques will also be covered.

"We're honored to be an invited speaker at this year's conference," said Fisch. "I look forward to a healthy discussion on the scalability of Z-RAM technology and how it aligns with the current SOI roadmap."

About Innovative Silicon

Innovative Silicon Inc. (ISi) delivers ultra-high density memory IP for embedded SoC, MPU, stand-alone DRAM and portable consumer applications requiring low power, high density and high speed. Endorsed by IEEE Spectrum Magazine in January 2007 as the winning semiconductor technology, and again in April 2007 by winning its ACE award for Emerging Technology, ISi's Z-RAM® memory offers up to twice the density of embedded DRAM and is up to five times denser than embedded SRAM. The company closed its first round of VC funding in 2003, completed its first 90nm megabit Z-RAM memory designs in 2004, its first 65nm designs in 2005 and its first 45nm designs in 2006. With more than 20 patents already granted, Z-RAM®'s unique single-transistor architecture is the world's lowest cost semiconductor memory solution. The company is incorporated in the USA with R&D in Lausanne, Switzerland. For more information see www.z-ram.com.

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